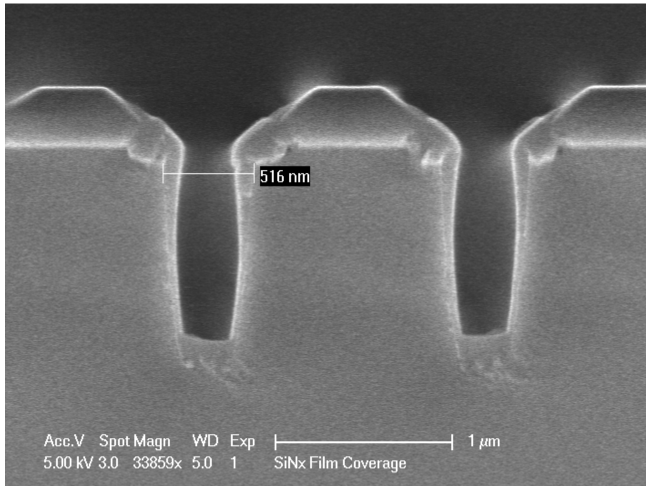

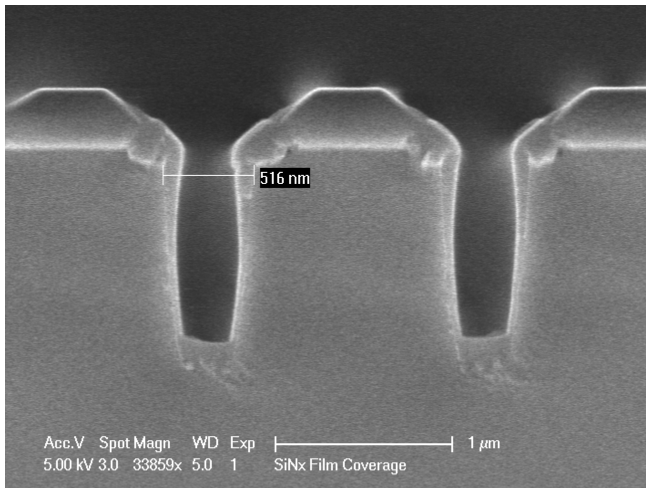

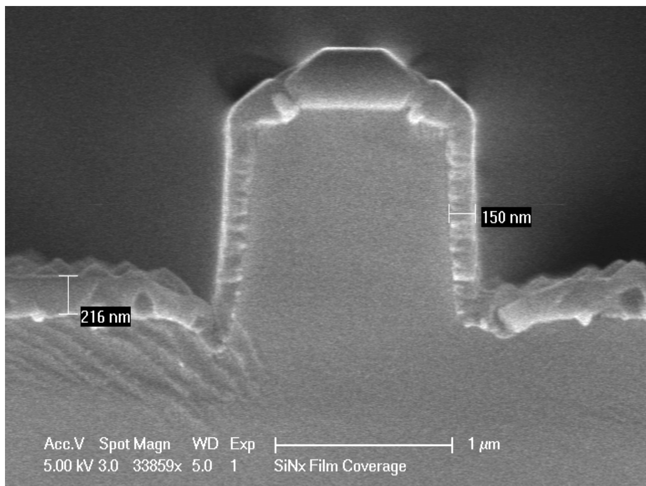

Figure 3 (a), (b), and (c) Side wall coverage of medium-stress SiNx film, deposited using Unaxis ICP tool at 100 ^{o}C, with chamber pressure=10 mT, bias/ICP powers=50 (94 V)/800 W, 100%SiH_4/N_2/Ar=15.5/8.5/20 sccm, and deposition time=266 s (One-minute buffered HF dip and Ar plasma clean prior to the deposition with pressure=10 mT, Ar flow rate=30 sccm, bias/ICP powers=20/800 W, and clean time=40 s).